



XC74WL00AASR

CMOS Logic

◆ CMOS Dual-Input NAND Gate

◆ Operating Voltage Range : 2V ~ 5.5V

◆ High Speed Operations : tpd = 2.6ns TYP

◆ Low Power Consumption : 1μA (max)

◆ MSOP-8B Package

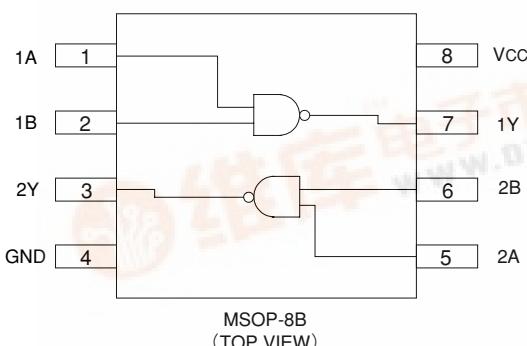
Description

XC74WL00AASR is a dual 2-input CMOS NAND gate, manufactured using silicon gate CMOS processes. The small quiescent current, which is one of the features of the CMOS logic, gives way to high speed operations which enables LS-TTL.

With wave forming buffers connected internally, stabilized output can be achieved as the series offers high noise immunity.

As the series is integrated into a mini molded, MSOP-8B package, high density mounting is possible.

Pin Configuration



Applications

- Palmtops

- Digital Equipment

Features

High Speed Operations : tpd = 2.6ns TYP (Vcc=5V)

Operating Voltage Range: 2V ~ 5.5V

Low Power Consumption: 1μA (max)

Small Package : MSOP-8B

Functions

INPUT		OUTPUT
A	B	Y
H	H	L
H	L	H
L	H	H
L	L	H

H = High Level

L = Low Level

Absolute Maximum Ratings

Ta = -40°C ~ 85°C

PARAMETER	SYMBOL	RATINGS	UNITS
Power Supply Voltage	VCC	-0.5~+6.0	V
Input Voltage	VIN	-0.5~+6.0	V
Output Voltage	VOUT	-0.5~VCC+0.5	V
Input Diode Current	I _{IK}	-20	mA
Output Diode Current	I _{OK}	±20	mA
Switch Output Current	I _{OUT}	±25	mA
VCC, GND Current	I _{CC} , I _{GND}	±50	mA
Power Dissipation (Ta = 25°C)	Pd	300	mW
Storage Temperature	T _{STG}	-65~+150	°C

Note : Voltage is all Ground standardized.

■ Recommended Operating Conditions

PARAMETER	SYMBOL	CONDITIONS			UNITS
Supply Voltage	VCC	2~5.5			V
Input Voltage	VIN	0~5.5			V
Output Voltage	VOUT	0~VCC			V
Operating Temperature	Topr	−40~+85			°C
Input Rise/Fall Time	tr, tf	0~200 (VCC=3.3V) 0~100 (VCC=5V)			ns

■ DC Electrical Characteristics

PARAMETER	SYMBOL	CONDITIONS		Ta=25°C			Ta=−40~85°C		UNITS
				MIN	TYP	MAX	MIN	MAX	
Input Voltage	VIH	VCC (V)	VIN=VIL or VIH	1.5	—	—	1.5	—	V
		2.0		2.1	—	—	2.1	—	
		3.0		3.85	—	—	3.85	—	
	VIL	2.0		—	—	0.5	—	0.5	V
		3.0		—	—	0.9	—	0.9	
		5.5		—	—	1.65	—	1.65	
	VOH	2.0		1.9	2.0	—	1.9	—	V
		3.0		2.9	3.0	—	2.9	—	
		4.5		4.4	4.5	—	4.4	—	
		3.0		2.58	—	—	2.48	—	
		4.5		3.94	—	—	3.80	—	
Output Voltage	VOL	2.0	IOH=−50 μA	—	—	0.1	—	0.1	V
		3.0		—	—	0.1	—	0.1	
		4.5		—	—	0.1	—	0.1	
		3.0		—	—	0.36	—	0.44	
		4.5		—	—	0.36	—	0.44	
	VOL	2.0	IOL=50 μA	—	—	0.1	—	0.1	V
		3.0		—	—	0.1	—	0.1	
		4.5		—	—	0.1	—	0.1	
		3.0		—	—	0.36	—	0.44	
		4.5		—	—	0.36	—	0.44	
Input Voltage	IIN	0~5.5	VIN=VCC or GND	−0.1	—	0.1	−1.0	1.0	μA
Quiescent Supply Current	ICC	5.5	VIN=VCC or GND, IOUT=0 μA	—	—	1.0	—	10.0	μA

■ Switching Electrical Characteristics

(tr=tf=3ns)

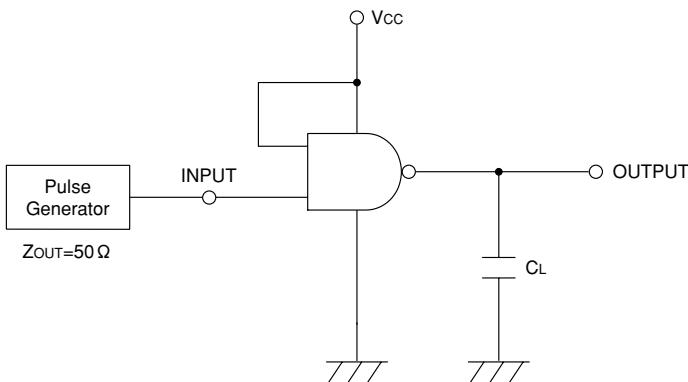
PARAMETER	SYMBOL	CONDITIONS		Ta=25°C			Ta=−40~85°C		UNITS	
				MIN	TYP	MAX	MIN	MAX		
Propagation Delay Time	tPLH	CL	3.3	VIN=VCC or GND	—	3.7	7.9	1	9.5	ns
			5.0		—	2.7	5.5	1	6.5	
		50pF	3.3		—	5.4	11.4	1	13	ns
			5.0		—	3.6	7.5	1	8.5	
	tPHL	CL	3.3		—	3.3	7.9	1	9.5	ns
			5.0		—	2.5	5.5	1	6.5	
		50pF	3.3		—	4.6	11.4	1	13	ns
			5.0		—	3.5	7.5	1	8.5	
Input Capacitance	CIN	—	5.0	VIN=VCC or GND	—	2	10	—	10	pF
Power Dissipation	Cpd	No Load, f=1MHz			—	9.3	—	—	—	pF

■Noise Characteristics

(tr=tf=3ns)

PARAMETER	SYMBOL			CONDITIONS	Ta=25°C			UNITS
		CL	Vcc(V)		MIN	TYP	MAX	
Not functioning output maximum dynamic VOL	VOLP	50pF	5.0		—	0.3	0.8	V
Not functioning output minimum dynamic VOL	VOLV	50pF	5.0		-0.8	-0.3	—	V
Minimum dynamic VIH	VIHD	50pF	5.0		—	—	3.5	V
Maximum dynamic Vil	VILD	50pF	5.0		—	—	1.5	V

■Typical Application Circuit



■Waveforms

